

NOR Flash Parallel 3V/3.3V 2G-bit 256M x 8/128M x 16 110ns 64-Pin Fortified BGA Tray



Images are for reference only

Manufacturer: [Infineon Technologies Corporation](#)

Package/Case: BGA64

Product Type: Memory

RoHS: RoHS Compliant/Lead free 

Lifecycle: Active

[Inquiry](#)

General Description

The S70GL02GT 2-Gb MIRRORBIT™ flash memory device is fabricated on 45-nm MIRRORBIT™ process technology. This device offers a fast page access time of 20 ns with a corresponding random access time of 110 ns. It features a write buffer that allows a maximum of 256 words/512 bytes to be programmed in one operation, resulting in faster effective programming time than standard single byte/word programming algorithms. This makes the device an ideal product for today's embedded applications that require higher density, better performance and lower power consumption.

Key Features

CMOS 3.0 V core with versatile I/O

- Two 1024 Mb (S29GL01GT) in a single 64-ball fortified-BGA package (see the S29GL01GT datasheet for full specifications)
- 45 nm MIRRORBIT™ process technology
- Single supply (VCC) for read/program/erase (2.7 V to 3.6 V)
- Versatile I/O feature
 - Wide I/O voltage (VIO): 1.65 V to VCC
- ×8 and ×16 data bus
- 16-word/32-byte page read buffer
- 512-byte programming buffer
 - Programming in page multiples, up to a maximum of 512 bytes
- Sector erase
 - Uniform 128-KB sectors
 - S70GL02GT: 2048 sectors
- Suspend and Resume commands for program and erase operations
- Status Register, data polling, and ready/busy pin methods to determine device status
- Advanced sector protection (ASP)
 - Volatile and non-volatile protection methods for each sector
- Separate 1024-byte one time program (OTP) array with two lockable regions
 - Each device supports common flash interface (CFI)
- WP# input
 - Protects the last sector of the device, regardless of sector protection settings

Performance characteristics

- Temperature range/grade
 - Industrial (−40°C to +85°C)
 - Industrial Plus (−40°C to +105°C)
 - Automotive, AEC-Q100 grade 3 (−40°C to +85°C)
 - Automotive, AEC-Q100 grade 2 (−40°C to +105°C)
- 100,000 program-erase cycles
- 20-year data retention
- Packaging options
 - 64-ball LSH fortified BGA, 13 mm × 11 mm

Recommended For You

S71KS512SC0BHV000

Infineon Technologies Corporation
24-FBGA

S70KS1281DPBH020

Infineon Technologies Corporation
BGA

S70KL1281DABH023

Infineon Technologies Corporation
BGA

S71VS128RC0AHK4L0

Infineon Technologies Corporation
BGA

S70FL01GSAGMFB010

Infineon Technologies Corporation
SOP16

S79FS01GSFABHB210

Infineon Technologies Corporation
BGA24

S70KL1282GABHV020

Infineon Technologies Corporation

BGA

S70KS1282GABHI020

Infineon Technologies Corporation

QFN

S72NS256RD0AHBM00

Infineon Technologies Corporation

FBGA-133

S71KS512SC0BHB000

Infineon Technologies Corporation

BGA24

S71GL064NB0BHW0P0

Infineon Technologies Corporation

BGA

S71VS256RD0AHK400

Infineon Technologies Corporation

BGA

S72VS256RE0AHBH10

Infineon Technologies Corporation

BGA

S71KL512SC0BHV000

Infineon Technologies Corporation

BGA24

S71VS064RB0AHTCL0

Infineon Technologies Corporation

BGA